L Number	Hits	Search Text	DB	Time stamp
163	6673	((impurity or doping) adj (density))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:49
164	908	((impurity or doping) adj (density)) and junction and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:49
165	212	((impurity or doping) adj (density)) and junction and diode and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:49
166	8	((impurity or doping) adj (density)) same junction same diode same polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:54
167	46	((impurity or doping) adj (density or concentration)) same junction same diode same polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:54
168	39	(US-5942933-$ or US-5386138-$ or US-6333535-$ or US-6545360-$ or US-6352882-$ or US-6121661-$ or US-5160987-$ or US-6587370-$ or US-6204518-$ or US-5962900-$ or US-5907778-$ or US-5686736-$ or US-5266831-$ or US-6320474-$ or US-4169270-$ or US-4103415-$ or US-5891778-$ or US-4958209-$ or US-6759700-$ or US-6692998-$ or US-6455378-$ or US-5666077-$ or US-5422299-$ or US-4300212-$).did. or (US-20010045665-$ or US-20020031916-$ or US-20020057594-$ or US-20020125541-$ or US-20020043687-$ or US-20020074483-$ or US-20020063288-$).did. or (JP-05283715-$ or JP-07245344-$ or JP-04069939-$ or JP-04034982-$).did. or (US-5386138-$ or JP-05283715-$ or JP-2001257349-$ or GB-2218565-$).did.	USPAT; US-PGPUB; JPO; DERWENT	2004/09/02 16:54

| 170 | 0 | ((US-5942933-$ or US-5386138-$ or US-6333535-$ or US-6545360-$ or US-6352882-$ or US-6121661-$ or US-5160987-$ or US-6587370-$ or US-6204518-$ or US-5962900-$ or US-5907778-$ or US-5686736-$ or US-5266831-$ or US-6320474-$ or US-4169270-$ or US-4103415-$ or US-5891778-$ or US-4958209-$ or US-6759700-$ or US-6692998-$ or US-6455378-$ or US-5666077-$ or US-5422299-$ or US-4300212-$).did. or (US-20010045665-$ or US-20020031916-$ or US-20020057594-$ or US-20020125541-$ or US-20020043687-$ or US-20020074483-$ or US-20020063288-$).did. or (JP-05283715-$ or JP-07245344-$ or JP-04069939-$ or JP-04034982-$).did. or (US-5386138-$ or JP-05283715-$ or JP-2001257349-$ or GB-2218565-$).did.) and (((impurity or doping) adj (density or concentration)) near5 (equal or similar)) same junction same diode same polysilicon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/02 16:55 |
| 171 | 0 | ((US-5942933-$ or US-5386138-$ or US-6333535-$ or US-6545360-$ or US-6352882-$ or US-6121661-$ or US-5160987-$ or US-6587370-$ or US-6204518-$ or US-5962900-$ or US-5907778-$ or US-5686736-$ or US-5266831-$ or US-6320474-$ or US-4169270-$ or US-4103415-$ or US-5891778-$ or US-4958209-$ or US-6759700-$ or US-6692998-$ or US-6455378-$ or US-5666077-$ or US-5422299-$ or US-4300212-$).did. or (US-20010045665-$ or US-20020031916-$ or US-20020057594-$ or US-20020125541-$ or US-20020043687-$ or US-20020074483-$ or US-20020063288-$).did. or (JP-05283715-$ or JP-07245344-$ or JP-04069939-$ or JP-04034982-$).did. or (US-5386138-$ or JP-05283715-$ or JP-2001257349-$ or GB-2218565-$).did.) and (((impurity or doping) adj (density or concentration)) near5 (equal or similar)) and junction same diode same polysilicon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/02 16:55 |

| 172 | 0 | ((US-5942933-$ or US-5386138-$ or US-6333535-$ or US-6545360-$ or US-6352882-$ or US-6121661-$ or US-5160987-$ or US-6587370-$ or US-6204518-$ or US-5962900-$ or US-5907778-$ or US-5686736-$ or US-5266831-$ or US-6320474-$ or US-4169270-$ or US-4103415-$ or US-5891778-$ or US-4958209-$ or US-6759700-$ or US-6692998-$ or US-6455378-$ or US-5666077-$ or US-5422299-$ or US-4300212-$).did. or (US-20010045665-$ or US-20020031916-$ or US-20020057594-$ or US-20020125541-$ or US-20020043687-$ or US-20020074483-$ or US-20020063288-$).did. or (JP-05283715-$ or JP-07245344-$ or JP-04069939-$ or JP-04034982-$).did. or (US-5386138-$ or JP-05283715-$ or JP-2001257349-$ or GB-2218565-$).did.) and (((impurity or doping) adj (density or concentration)) near5 (equal or similar)) and junction and diode same polysilicon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/02 16:55 |
| 173 | 0 | ((US-5942933-$ or US-5386138-$ or US-6333535-$ or US-6545360-$ or US-6352882-$ or US-6121661-$ or US-5160987-$ or US-6587370-$ or US-6204518-$ or US-5962900-$ or US-5907778-$ or US-5686736-$ or US-5266831-$ or US-6320474-$ or US-4169270-$ or US-4103415-$ or US-5891778-$ or US-4958209-$ or US-6759700-$ or US-6692998-$ or US-6455378-$ or US-5666077-$ or US-5422299-$ or US-4300212-$).did. or (US-20010045665-$ or US-20020031916-$ or US-20020057594-$ or US-20020125541-$ or US-20020043687-$ or US-20020074483-$ or US-20020063288-$).did. or (JP-05283715-$ or JP-07245344-$ or JP-04069939-$ or JP-04034982-$).did. or (US-5386138-$ or JP-05283715-$ or JP-2001257349-$ or GB-2218565-$).did.) and (((impurity or doping) adj (density or concentration)) near5 (equal or similar)) and junction and diode and polysilicon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/02 16:55 |

174	0	(((US-5942933-$ or US-5386138-$ or US-6333535-$ or US-6545360-$ or US-6352882-$ or US-6121661-$ or US-5160987-$ or US-6587370-$ or US-6204518-$ or US-5962900-$ or US-5907778-$ or US-5686736-$ or US-5266831-$ or US-6320474-$ or US-4169270-$ or US-4103415-$ or US-5891778-$ or US-4958209-$ or US-6759700-$ or US-6692998-$ or US-6455378-$ or US-5666077-$ or US-5422299-$ or US-4300212-$).did. or (US-20010045665-$ or US-20020031916-$ or US-20020057594-$ or US-20020125541-$ or US-20020043687-$ or US-20020074483-$ or US-20020063288-$).did. or (JP-05283715-$ or JP-07245344-$ or JP-04069939-$ or JP-04034982-$).did. or (US-5386138-$ or JP-05283715-$ or JP-2001257349-$ or GB-2218565-$).did.) and (((impurity or doping) adj (density or concentration)) near10 (equal or similar)) and junction and diode and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:55
175	170	(((impurity or doping) adj (density or concentration)) near10 (equal or similar)) and junction and diode and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:56
176	24	(((impurity or doping) adj (density or concentration)) near10 (equal or similar)).ti,ab,clm. and junction and diode and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:56
177	11	(((impurity or doping) adj (density or concentration)) near10 (equal or similar)).ti,ab,clm. and junction.ti,ab,clm. and diode and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:56
179	0	(((impurity or doping) adj (density or concentration)) near10 (equal or similar)).ti,ab,clm. and junction.ti,ab,clm. and diode.ti,ab,clm. and polysilicon.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:56
178	1	(((impurity or doping) adj (density or concentration)) near10 (equal or similar)).ti,ab,clm. and junction.ti,ab,clm. and diode.ti,ab,clm. and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:57
180	9	(((impurity or doping) adj (density or concentration)) near10 (equal or similar or substantially)).ti,ab,clm. and junction.ti,ab,clm. and diode.ti,ab,clm. and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:58

181	1	(((impurity or doping) adj (density or concentration)) near10 (equal or similar or substantially)).ti,ab,clm. and junction.ti,ab,clm. and diode.ti,ab,clm. and (polysilicon near5 (plug or trench or via or hole or opening))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:59
183	1	(((impurity or doping) adj (density or concentration)) near10 (equal or similar or substantially)) and junction.ti,ab,clm. and diode.ti,ab,clm. and (polysilicon near5 (plug or trench or via or hole or opening)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 17:00
182	7	(((impurity or doping) adj (density or concentration)) near10 (equal or similar or substantially)) and junction.ti,ab,clm. and diode.ti,ab,clm. and (polysilicon near5 (plug or trench or via or hole or opening))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 17:00
184	40	(US-5942933-$ or US-5386138-$ or US-6333535-$ or US-6545360-$ or US-6352882-$ or US-6121661-$ or US-5160987-$ or US-6587370-$ or US-6204518-$ or US-5962900-$ or US-5907778-$ or US-5686736-$ or US-5266831-$ or US-6320474-$ or US-4169270-$ or US-4103415-$ or US-5891778-$ or US-4958209-$ or US-6759700-$ or US-6692998-$ or US-6455378-$ or US-5666077-$ or US-5422299-$ or US-4300212-$ or US-5119148-$).did. or (US-20010045665-$ or US-20020031916-$ or US-20020057594-$ or US-20020125541-$ or US-20020043687-$ or US-20020074483-$ or US-20020063288-$).did. or (JP-05283715-$ or JP-07245344-$ or JP-04069939-$ or JP-04034982-$).did. or (US-5386138-$ or JP-05283715-$ or JP-2001257349-$ or GB-2218565-$).did.	USPAT; US-PGPUB; JPO; DERWENT	2004/09/02 17:01

185	4	((US-5942933-$ or US-5386138-$ or US-6333535-$ or US-6545360-$ or US-6352882-$ or US-6121661-$ or US-5160987-$ or US-6587370-$ or US-6204518-$ or US-5962900-$ or US-5907778-$ or US-5686736-$ or US-5266831-$ or US-6320474-$ or US-4169270-$ or US-4103415-$ or US-5891778-$ or US-4958209-$ or US-6759700-$ or US-6692998-$ or US-6455378-$ or US-5666077-$ or US-5422299-$ or US-4300212-$ or US-5119148-$).did. or (US-20010045665-$ or US-20020031916-$ or US-20020057594-$ or US-20020125541-$ or US-20020043687-$ or US-20020074483-$ or US-20020063288-$).did. or (JP-05283715-$ or JP-07245344-$ or JP-04069939-$ or JP-04034982-$).did. or (US-5386138-$ or JP-05283715-$ or JP-2001257349-$ or GB-2218565-$).did.) and ((substantially or equal or similar or identical) near5 (density or concentration))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 17:02
186	0	((substantially or equal or similar or identical) near5 (density or concentration)) and (polysilicon near plug) and (((p-n) or pn) near junction near diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 17:03
187	0	((substantially or equal or similar or identical) near5 (density or concentration)) and (polysilicon near (trench or plug)) and (((p-n) or pn) near junction near diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 17:03
188	3	((substantially or equal or similar or identical) near5 (density or concentration)) and (polysilicon near3 (trench or plug)) and (((p-n) or pn) near junction near diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 17:05
189	7	((substantially or equal or similar or identical) near5 (density or concentration)) and (polysilicon near3 (trench or plug)) and (((p-n) or pn) near2 junction near2 diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 17:05

L Number	Hits	Search Text	DB	Time stamp
132	45	((impurity or doping) near (density or concentration)) and ((junction near diode) with polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:30
133	8	((impurity or doping) near (density or concentration)) and ((junction near diode) with polysilicon with (trench or via or hole or plug))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:31
134	50289	((p-n) or pn) adj junction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:32
135	892	(((p-n) or pn) adj junction) and (polysilicon near3 (plug or via or hole or trench))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:32
136	54	(((p-n) or pn) adj junction).ti,ab,clm. and (polysilicon near3 (plug or via or hole or trench)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:33
137	8	(((p-n) or pn) adj junction).ti,ab,clm. and (polysilicon near3 (plug or via or hole or trench)).ti,ab,clm. and diode.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:36
138	0	(((p-n) or pn) adj junction).ti,ab,clm. and (polysilicon near3 (plug or via or hole or trench) near3 type).ti,ab,clm. and diode.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:36
139	1	(((p-n) or pn) adj junction).ti,ab,clm. and (polysilicon near3 (plug or via or hole or trench) near3 (doped or type)).ti,ab,clm. and diode.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/02 16:36